[FC2] Plasma & Atomic Layer Etching Ⅱ	
Date / Time	July 27 (Fri.), 2018 / 13:40-15:00
Place	Room C (#114)
Session Chair(s)	Nam Hun Kim (Adaptive Plasma Tech. Corp., Korea) Thorsten Lill (Lam Research Corp., USA)

FC2-1 [Invited] **13:40-14:10**

Atomic Layer Defect-Free Top-Down Processes for Future Nano-Devices

Seiji Samukawa

Tohoku Univ., Japan

FC2-2 **14:10-14:30**

Surface Reaction Mechanisms of Hexafluoroacetylacetone (HFAC) on a Nickel or Nickel Oxide Surface for Atomic-Layer Etching (ALE)

Abdulrahman Hikmat Basher[1], Michiro Isobe[1], Tomoko Ito[1], Kazuhiro Karahashi[1], Masato Kiuchi[2], Takae Takeuchi[3], and Satoshi Hamaguchi[1]

[1]*Osaka Univ., Japan,* [2]*AIST, Japan,* [3]*Nara Women's Univ., Japan*

FC2-3 [Invited] **14:30-15:00**

Isotropic Atomic Layer Etching of ZnO on 2D and 3D Substrates Using Acetylacetone and O_2 Plasma

Alfredo Mameli[1], Marcel A. Verheijen[1], Adrie J.M. Mackus[1], Erwin (W.M.M.) Kessels[1], and Fred Roozeboom[1,2]

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